

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A fabrication method of a liquid crystal display panel, comprising:

forming a thin film transistor at crossings of gate lines and data lines formed on a substrate in a first masking process,

~~a pixel electrode, and~~

providing a substrate including a plurality of thin film transistor array substrates having a gate pad part formed thereon including a gate pad connected to the gate line, [[and]] a data pad part including a data pad connected to the data line in a second masking process[[,]]; [[and]]

forming a data pad protection electrode and forming a pixel electrode in a third masking process, and;

arranging a cutting-off plate on a remainder region of the substrate other than the region of the pad part; and

exposing the gate pad of the pad part and the data pad protection electrode by a etching process using the cutting-off plate.

2. (Original) The fabrication method of the liquid crystal display panel according to claim 1, wherein a step of assembling a thin film transistor array substrate and a color filter array substrate where the gate pad and the data pad protection electrode are exposed, is further comprised.

3. (Original) The fabrication method of the liquid crystal display panel according to claim 1, wherein the cutting-off plate is made of a metal.

4. (Previously Presented) The fabrication method of the liquid crystal display panel according to claim 1, wherein the step of forming the thin film transistor array substrate comprises the steps of:

forming a gate pattern including a gate electrode of the thin film transistor, a gate line connected to the gate electrode and a gate pad connected to the gate line on the substrate by use of a masking process;

forming a gate insulation film on the substrate where the gate pattern is formed;

forming a source electrode and a drain electrode of the thin film transistor, a data line connected to the source electrode, a data pad connected to the data line, a source/drain pattern including a storage electrode in a region overlapped with the gate line, a semiconductor pattern formed in the lower part according to the source/drain pattern on the gate insulation film by use of a second masking process; and

forming a pixel electrode connected to the drain electrode and the storage electrode, a transparent electrode pattern including a data pad protection electrode formed for covering the data pad and a protection film on the substrate where the transparent electrode pattern is formed by a third masking process.

5. (Previously Presented) The fabrication method of the thin film transistor panel according to claim 4 wherein the step of exposing the gate pad of the gate pad part comprises the step of removing the insulation film and the gate insulation part formed in the gate pad part by use of dry etching process.

6. (Previously Presented) The fabrication method of the thin film transistor panel according to claim 4, wherein the step of exposing the data pad protection electrode of the data pad part comprises the step of removing the insulation film formed on the data pad part and the gate insulation film not overlapped with the data pad protection electrode by dry etching process.